

IN THE SPECIFICATION

Please replace the paragraph beginning at page 3, line 19 with the following paragraph:

Fig 2 illustrates a device structure in accordance with an embodiment of the invention. Again, the device, 30, includes a laser, 31, a modulator, 32, and an SOA, 33, integrated onto a single substrate, 33-34. As before, each component, 31-33, comprises a cladding/SCL layer, 35, an active layer, 36, and another cladding/SCL layer 37. However, rather than provide interconnection of the components by means of an active waveguide, the interconnections are made by a structure, 41 and 42, which includes a passive waveguide layer, 43. In this particular example, the passive waveguide layer, 43, is sandwiched between SCL layers, 44 and 45. In a preferred embodiment, the layers 43-45, can be formed sequentially in all the areas between components at the same time, i.e., the same layers will comprise the interconnections between all components. The device, 30, also preferentially includes a layer, 46, formed over essentially the entire substrate surface. The layer comprises a composition, such as InGaAsP, which can perform the function of a stop etch in the processing to be described.